

ECE4740: Digital VLSI Design

Lecture 13: Worst-case and
best-case delays

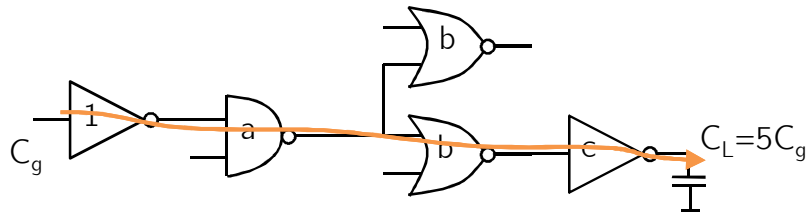
472

Another one

Sizing example

473

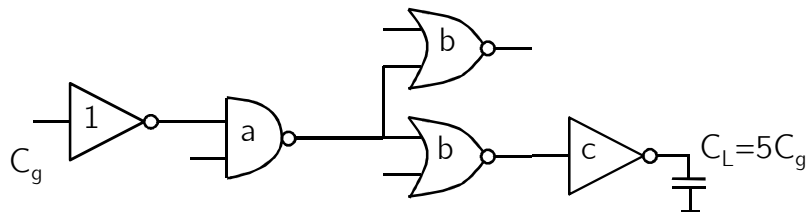
Start with a simple digital circuit



- Compute min. propagation delay
- Assume inverter PMOS:NMOS ratio of 2:1

474

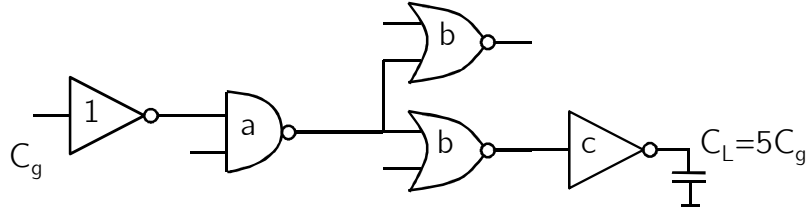
Compute key quantities



- Effective fan-out: $H=5$
- Path logical effort: $G=1*(4/3)*(5/3)*1$
- Path branching effort: $B=1*2*1*1$
- Total path effort: $F=H*G*B=22.22$
- Optimal gate effort: $f_{opt}=F^{1/4}=2.1712$

475

Calculate min. propagation delay



- Min. propagation delay:

$$t_p = t_{p0} \left(P + N \sqrt[N]{F} \right)$$

- $P=1+2+2+1=6$

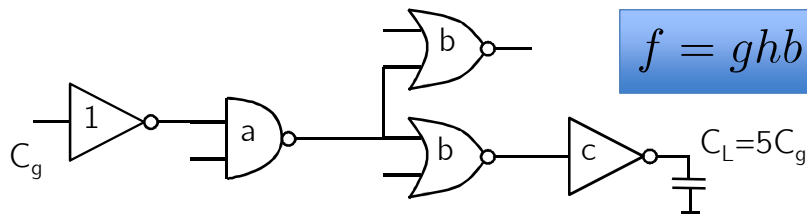
- $N \cdot f_{\text{opt}} = 8.6847$

sizing not required
for min. delay!

$$t_p = t_{p0} 14.68$$

476

Write down fan-outs

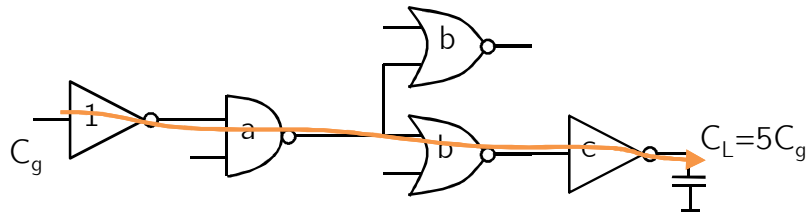


- $f_{\text{opt}} = 1 \cdot a \cdot 1 \rightarrow a = 2.17$
- $f_{\text{opt}} = (4/3) \cdot (b/a) \cdot 2 \rightarrow b = 1.76$
- $f_{\text{opt}} = (5/3) \cdot (c/b) \cdot 1 \rightarrow c = 2.3$
- **Final check:** $C_L/c = f_{\text{opt}} \rightarrow \text{YES}$

simpler gates are
used to drive more
capacitance!!

477

Size transistors



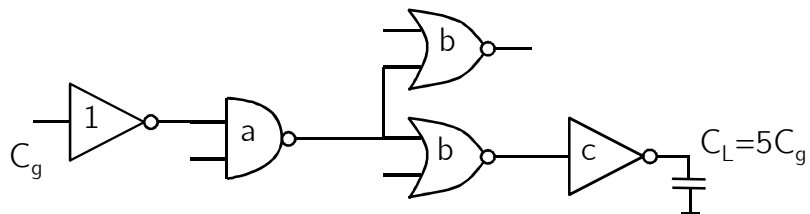
- Size transistors (PMOS/NMOS=2)
 - Hint: Use recursive formula from slide 606:

$$g_{i+1}s_{i+1} = \frac{h_i}{b_i} g_i s_i$$

sizing factor

478

Size transistors (cont'd)



- Begin from start to end and size iteratively

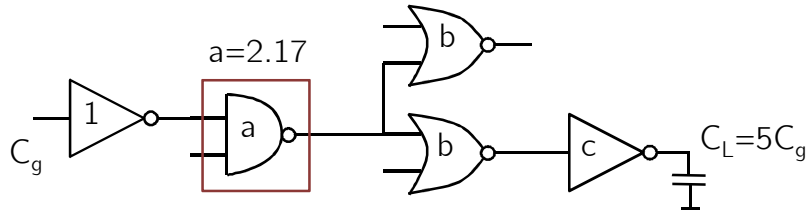
$$g_{i+1}s_{i+1} = \frac{h_i}{b_i} g_i s_i$$

sizing factor

- Here $s_1=1 \rightarrow$ proceed from left-to-right

479

Size transistors (cont'd)



- PMOS

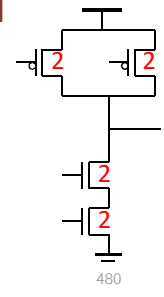
- $(W_p=2 \text{ to match inv.}) * a/g_2 = 3.25$

- NMOS

- $(W_n=2 \text{ to match inv.}) * a/g_2 = 3.25$

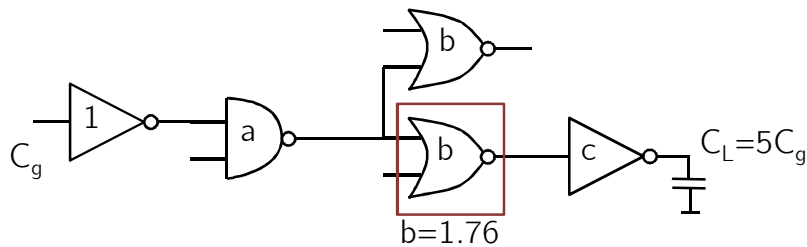
$$g_{i+1}s_{i+1} = \frac{h_i}{b_i} g_i s_i$$

remove own gate effort



480

Size transistors (cont'd)

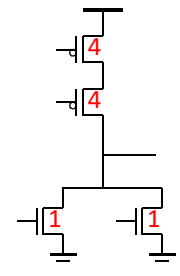


- PMOS

- $(W_p=4 \text{ to match inv.}) * b/(g_3) = 4.22$

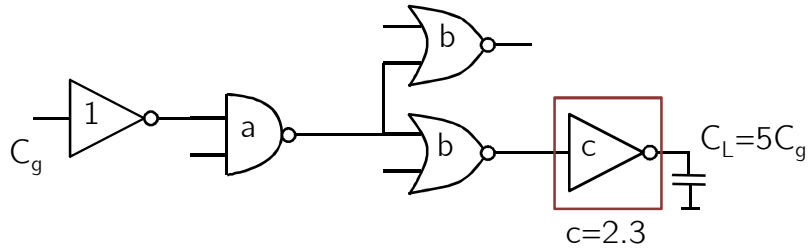
- NMOS

- $(W_n=1 \text{ to match inv.}) * b/(g_3) = 1.01$

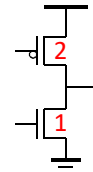


481

Size transistors (cont'd)



- PMOS
 - $(W_p=2 \text{ to match inv.}) * c/g_4=4.6$
- NMOS
 - $(W_n=1 \text{ to match inv.}) * c/g_4=2.3$



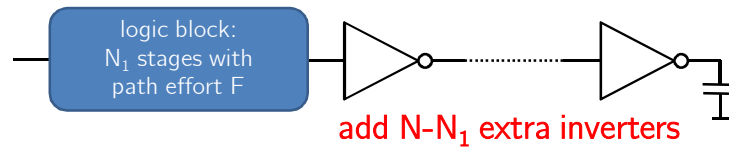
482

This time for CMOS gates

Optimal number of stages

483

Optimal number of stages



- Total (normalized) delay:

$$D = N \sqrt[N]{F} + \sum_{i=1}^{N_1} p_i + (N - N_1)p_{inv}$$

- Take derivative and set to zero:

$$p_{inv} + \rho(1 - \log(\rho)) = 0 \quad \leftarrow \quad \rho = \sqrt[N^*]{F}$$

optimal stage effort

N^* = best #
of stages

484

“Good” number of stages

- Formula has no closed-form solution
- Neglecting parasitics, e.g., p_{inv}
 - Optimal stage effort $\rho \approx 3.59$
- $2.4 < \rho < 6 \rightarrow$ delays within 15% of optimal
- $\rho = 4$ is usually a good pick
 - Rule of thumb for good number of stages:

$$\hat{N} = \log_4(F)$$

485

Recipe for sizing

1. Compute total path effort: $F=GHB$
2. Estimate “good” number of stages:

$$\hat{N} = \log_4(F)$$

3. Estimate (normalized) delay

if you are allowed
to add inverters!

$$D = \hat{N} \sqrt[\hat{N}]{F} + P$$

4. Sketch logic + additional inverters
5. Compute stage effort and size transistors

486

Limitations of logical effort approach

- Chicken-or-egg problem
 - Estimating delay depends on logic, which depends on minimum delay you actually want
- Simplistic model
 - Neglects effects of input slopes etc.
 - Optimizes for speed only
 - Not accurate (Cadence sweeps still required)
- **But: helps to make quick design decisions!**
 - Decisions can be made without actually sizing it

487

Important for timing analysis

Worst-case and best-case delays

488

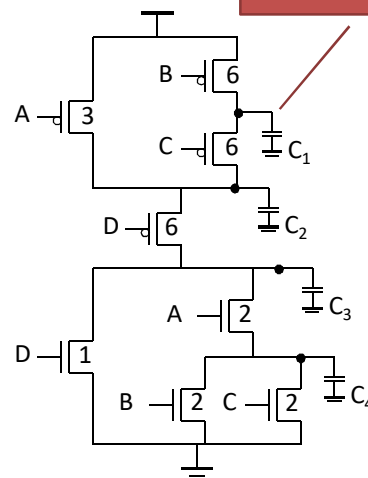
Worst-case delays

just consider
node
capacitances

- Worst-case delays depend on how many nodes are charged and how many need to be discharged

- Consider this gate:

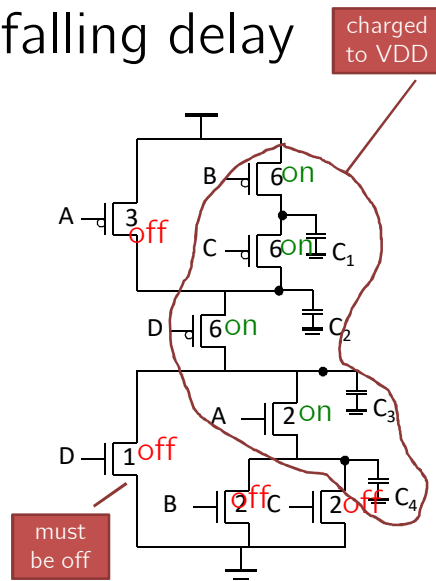
$$\text{out} = \overline{D + A(B + C)}$$



489

Worst-case falling delay

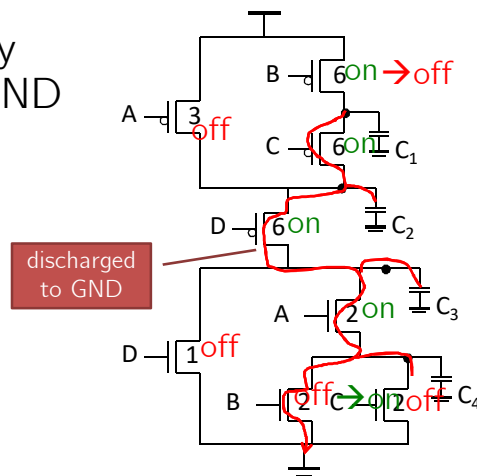
- Output must be 1
- Charge as many capacitances as you can to VDD
 - depends on sizing!
- [ABCD]=[1000]
- Total node caps at VDD: 6+6+6+2



490

Worst-case falling delay (cont'd)

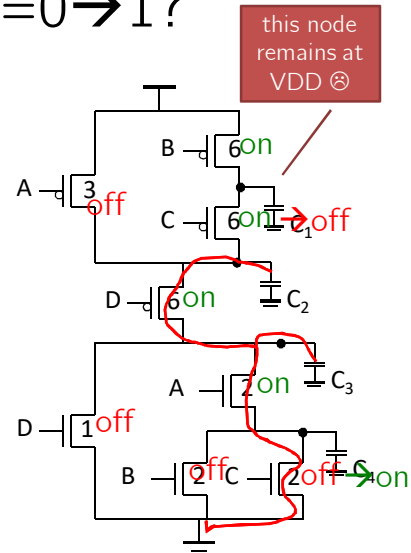
- Discharge as many capacitances to GND as you can
- Also discharge through weakest transistor!
- Initial state: [ABCD]=[1000]
- End state: [ABCD]=[1100]



491

Why not $C=0 \rightarrow 1$?

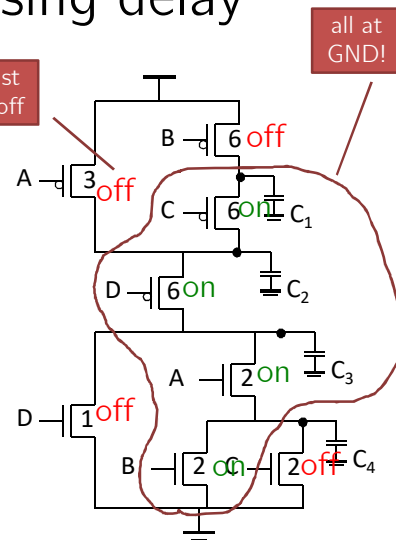
- Initial state:
[ABCD]=[1000]
- End state:
[ABCD]=[1010]
- Not the worst case:
fewer node caps
discharged!



492

Worst-case rising delay

- Output must be 0
- Discharge as many capacitances to GND as you can
- [ABCD]=[1100]
- Total discharged nodes: $6+6+2+2$

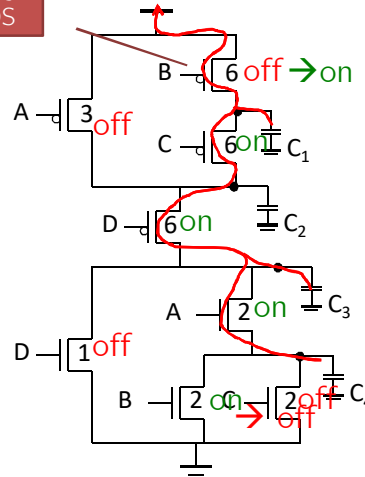


493

Worst-case rising delay (cont'd)

charged through strong PMOS

- Output must go to 1
- Charge as many capacitances as you can
- Initial state: [ABCD]=[1100]
- Final state: [ABCD]=[1000]



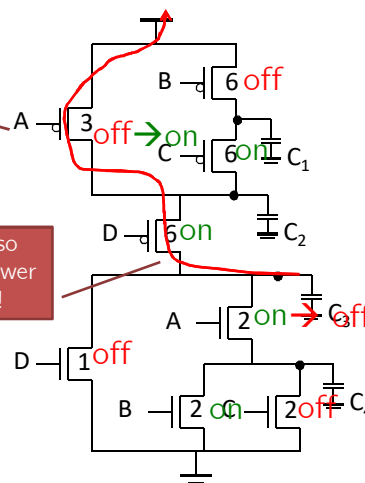
494

How about A=1→0?

charged through weaker PMOS

but also much fewer caps!

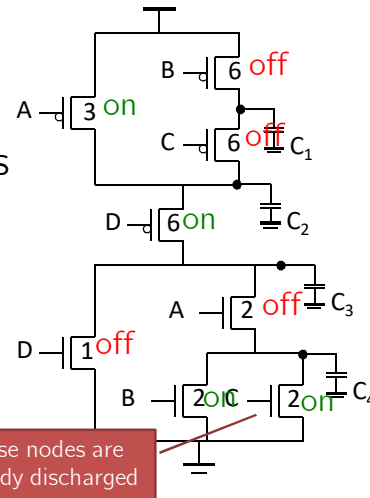
- Not the worst case!



495

Best-case falling delay

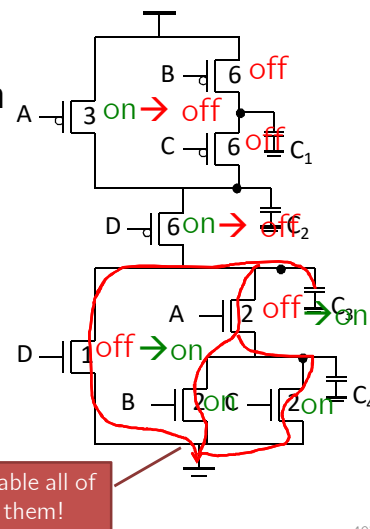
- Output must be 1
- **Discharge** as many capacitances to GND as you can
- $[ABCD]=[0110]$
- Total charged nodes: only 3+6



496

Best-case falling delay (cont'd)

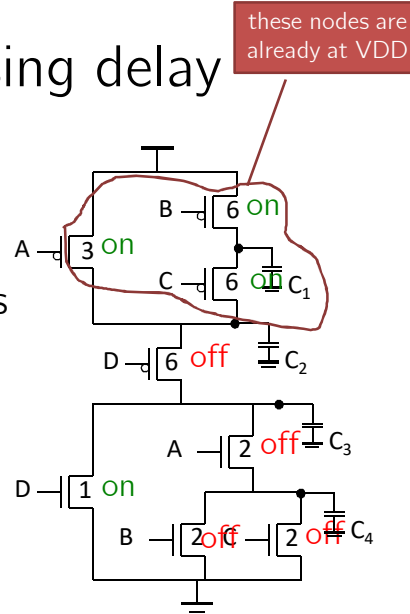
- **Discharge** as few capacitances as you can
- Discharge through **strongest NMOS**
- Initial state: $[ABCD]=[0110]$
- Final state: $[ABCD]=[1111]$



497

Best-case rising delay

- Output must be 0
- Charge as many capacitances to VDD as you can
- [ABCD]=[0001]

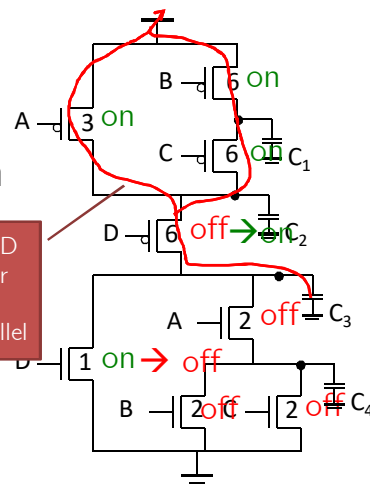


498

Best-case rising delay (cont'd)

- Output must go to 1
- Charge as few capacitances as you can
- Initial state: [ABCD]=[0001]
- Final state: [ABCD]=[0000]

charge to VDD much quicker through all PMOS in parallel



499